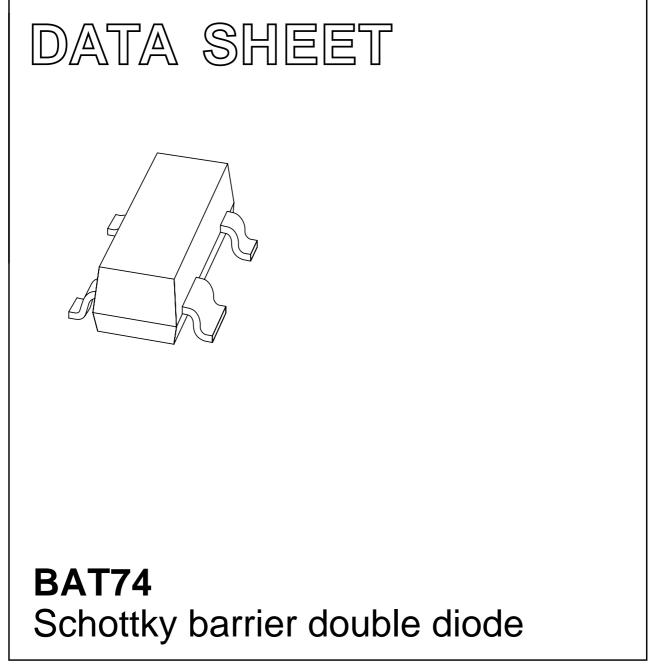
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of March 1991 1996 Mar 19



HILIP

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FEATURES

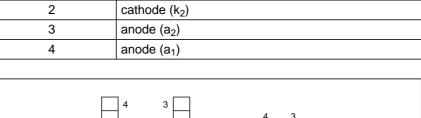
- Low forward voltage
- · Guard ring protected
- Small SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

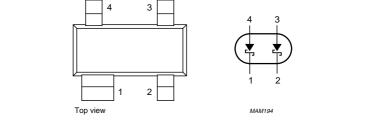
DESCRIPTION

Planar Schottky barrier double diode. Two separate dies encapsulated in a SOT143 small plastic SMD package.



cathode (k1)

DESCRIPTION



Marking code: L41.

PINNING

PIN

1

Fig.1 Simplified outline (SOT143), pin configuration and symbol.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode				•	
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \delta \le 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms		600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \text{ °C}$; see Fig.2	-	230	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C
Double die	ode operation			•	
V _R	continuous reverse voltage		_	30	V
		series connection	_	60	V
I _F	continuous forward current		-	110 ⁽¹⁾	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \delta \le 0.5$	_	200	mA

Note

1. If both diodes are in forward operation at the same moment, total device current is max. 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current is max. 200 mA.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT		
Per diode						
V _F	forward voltage	see Fig.3				
		I _F = 0.1 mA	240	mV		
		I _F = 1 mA; note 1	320	mV		
		I _F = 10 mA	400	mV		
		I _F = 30 mA	500	mV		
		I _F = 100 mA	800	mV		
I _R	reverse current	V _R = 25 V; note 2; see Fig.4	2	μA		
t _{rr}	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA; see Fig.6	5	ns		
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; \text{ see Fig.5}$	10	pF		

Notes

- 1. Temperature coefficient of forward voltage -0.6%/K.
- 2. Pulsed test: $t_p = 300 \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

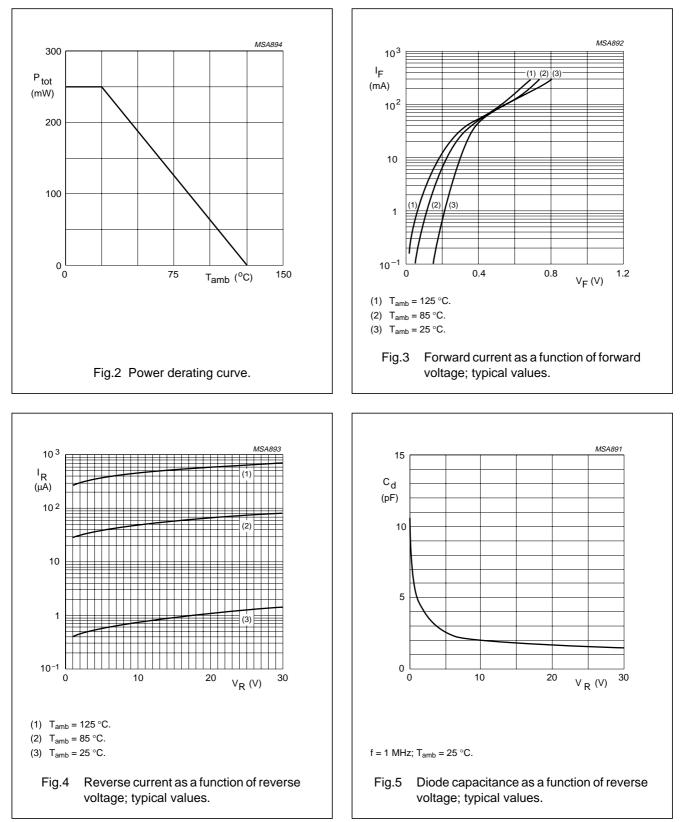
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Note

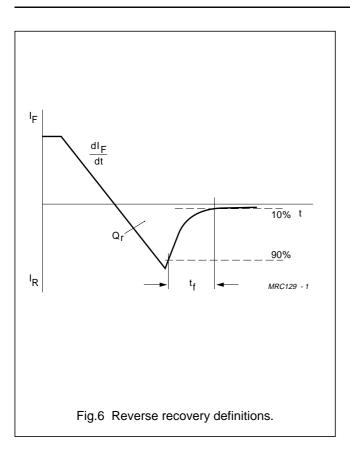
1. Refer to SOT143 standard mounting conditions

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GRAPHICAL DATA

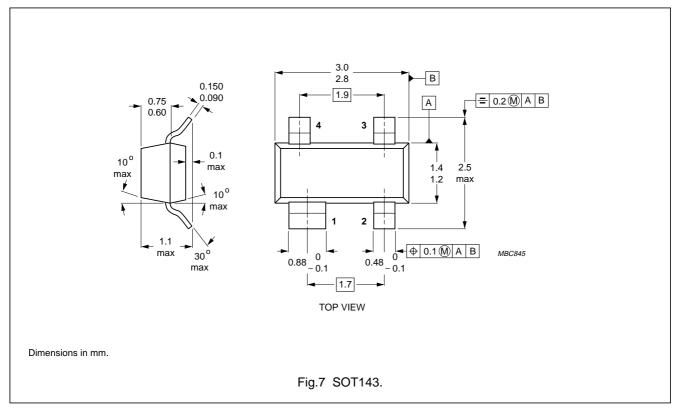


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PACKAGE OUTLINE



DEFINITIONS

Data sheet status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.